

SANYO	No.1290C	<h2 style="margin: 0;">2SA1348/2SC3402</h2> <p style="margin: 0;">PNP/ NPN Epitaxial Planar Silicon Transistors</p> <p style="margin: 0;">Switching Applications (with Bias Resistance)</p>
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Applications

Switching circuit, inverter, interface circuit, driver

Features

- Built-in bias resistor ($R_1=10k\Omega$, $R_2=10k\Omega$).
- Small-sized package (SPA).

(): 2SA1348

Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$

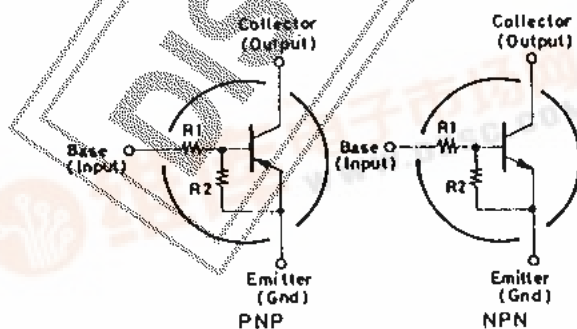
Collector to Base Voltage	V _{CB0}	(-)50	V
Collector to Emitter Voltage	V _{CE0}	(-)50	V
Emitter to Base Voltage	V _{EB0}	(-)10	V
Collector Current	I _C	(-)100	mA
Collector Current(Pulse)	I _{CP}	(-)200	mA
Collector Dissipation	P _C	300	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics/ $T_a=25^\circ\text{C}$

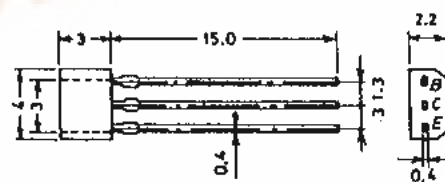
		min	typ	max	unit
Collector Cutoff Current	I _{CB0}			(-)0.1	μA
Collector Cutoff Current	I _{CE0}			(-)0.5	μA
Emitter Cutoff Current	I _{EB0}	(-)170	(-)250	(-)330	μA
DC Current Gain	h _{FE}	50			
Gain-bandwidth product	f _T		250 (200)		MHz
Output Capacitance	C _{ob}		3.7 (5.5)		pF
Collector to Emitter Saturation Voltage	V _{CE(sat)}		(-)0.1	(-)0.3	V

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Electrical Connection



Case Outline 2033
(unit: mm)



B: Base
C: Collector
E: Emitter
SANYO: SPA

Specifications and information herein are subject to change without notice.

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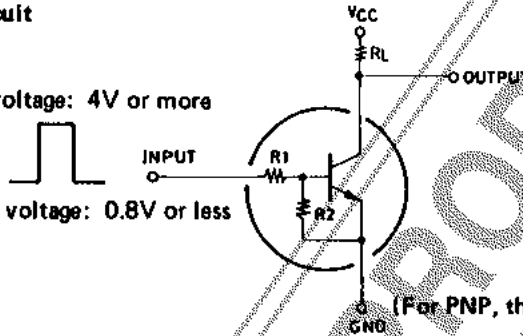
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			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)100\mu A, R_{BE} = \infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE} = (-)5V, I_C = (-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input On Voltage	$V_{I(on)}$	$V_{CE} = (-)0.2V, I_C = (-)10mA$	(-)1.0	(-)2.0	(-)4.0	V
Input Resistance	R_1		7.0	10	13	k Ω
Input Resistance Ratio	R_1/R_2		0.9	1.0	1.1	

■ Sample Application Circuit

Input ON-state voltage: 4V or more

Input OFF-state voltage: 0.8V or less



(For PNP, the polarity is reversed.)

